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FORESEE eMMC FEMKNN004G-58A42 Confidential Datasheet

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Rev. 1.2 FEMKNN004G-58A42

Revision History:

	Trevision thistory:									
Rev.	Date	Changes	organizer	Remark						
1.0	2020/02/28	Basic spec and architecture	XiuLiang Li	Draft						
1.1	2020/04/26	 Update the figure of package dimension and pin- assignment Add capacity information 	Glen Zhong	Preliminary						
1.2	2021/08/05	Update the parameters of performance and electrical characteristic	Glen Zhong							

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1. Introduction

FORESEE eMMC is an embedded storage solution designed in the BGA package. The FORESEE eMMC consists of NAND flash and eMMC controller. The controller could manage the interface protocols, wear-leveling, bad block management and ECC.

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FORESEE eMMC has high performance at a competitive cost, high quality and low power consumption, and eMMC is compatible with JEDEC standard eMMC 5.1 specifications.

2. Product List

Density	Part Number	NAND Flash Type	Capacity (bytes)	Capacity (MB)	Package Size(mm)	Package Type
4GB	ACB EEMKNINOOAC ESAAS	3,921,674,240		3740	9x7.5x0.8	153ball
4GB FEMKNN004G-58A42	32Gbit*1	3,921,074,240	3740	9x7.3x0.6	FBGA	

3. Features

> eMMC5.1 specification compatibility

(Backward compatible to eMMC4.41/4.5/5.0)

> Bus mode

- Data bus width: 1 bit (default), 4 bits, 8 bits

- MMC I/F Clock frequency: 0~200MHz

Operating voltage range

- Vcc(NAND) : 2.7 - 3.6V

- Vccq(Controller): 1.7 - 1.95V / 2.7 - 3.6V

> Temperature

- Operation (-25°C ~ +85°C)

- Storage without operation (-40°C ~ +85°C)

> Sudden-Power-Loss safeguard

> Hardware ECC engine

> Unique firmware backup mechanism

> Global-wear-leveling

- > Supported features.
 - HS400, HS200, SDR52
 - Partitioning, RPMB
 - Boot feature, boot partition
 - HW Reset/SW Reset
 - Discard, Trim, Erase, Sanitize
 - Background operations, HPI
 - Enhanced reliable write
 - S.M.A.R.T. Health Report
 - FFU
 - Sleep / awake

Others

1. - Compliance with the RoHS Directive







4. Functional Description

FORESEE eMMC with powerful L2P (Logical to Physical) NAND Flash management algorithm provides unique functions:

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- > Host independence from details of operating NAND flash
- > Internal ECC to correct defect in NAND flash
- Sudden-Power-Loss safeguard

To prevent from data loss, a mechanism named Sudden-Power-Loss safeguard is added in the eMMC. In the case of sudden power-failure, the eMMC would work properly after power cycling.

- Global-wear-leveling
 - To achieve the best stability and device endurance, this eMMC equips the Global Wear Leveling algorithm. It ensures that not only normal area, but also the frequently accessed area, such as FAT, would be programmed and erased evenly.
- > IDA(Initial Data Acceleration)
- 2. The eMMC prevents the pre-burned data from data-loss with IDA, in case of our customer had pre-burned data to eMMC, before the eMMC being SMT.
 - Cache

The eMMC enhanced the data written performance with Cache, with which our customer would get more endurance and reliability.

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5. Product Specifications

5.1 Performance

Density	Read	Write(cache off)	Write(cache on)	
4GB	60MB/s	15 MB/s	55MB/s	

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• Test Condition: Bus width x8, 200MHz DDR, 512KB data transfer, w/o file system overhead, measured on internal board

• Test tool: Crystaldiskmark 6.0.0

• Test size: 1GB

5.2 Power Consumption

5.2.1 Active power consumption during operation

Density	Icc	Iccq		
4GB	25mA	45mA		

• Power Measurement conditions: Bus configuration =x8 @200MHz DDR, 25°C.

Vcc:3.3V & Vccq: 1.8V.

The measurement for max RMS current is the average RMS current consumption over a period of 100ms.

5.2.2 Low power mode (stand-by)

ode (stand-by)							
Density	Icc	Iccq					
4GB	40uA	80uA					

- Power Measurement conditions: Bus configuration =x8 @200MHz DDR, 25°C.
- Standby: Nand Vcc & Controller Vccq power supply is switched on.
- The measurement for max RMS current is the average RMS current consumption over a period of 100ms.

5.2.3 Low power mode (sleep)

Density	Icc	Iccq
4GB	0	80uA

- Power Measurement conditions: Bus configuration =x8 @200MHz DDR, 25℃.
- Sleep: Nand Vcc power supply is switched off(Controller Vccq on)
- The measurement for max RMS current is the average RMS current consumption over a period of 100ms.







6. Pin Assignments

.6.1 Ball Array view

	1	2	3	4	5	6	7	8	9	10	11	12	13	14
Α	\bigcirc	\bigcirc	(рато)	(DAT)	(БАТ)	(Vss)	(RFU)	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc
В	\bigcirc	DAT3	DAT4	DATE	DATE	DAT	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc
С	\bigcirc	VDD	\bigcirc	Vss	\bigcirc	VDD	\bigcirc	\bigcirc	\bigcirc		\bigcirc	\bigcirc	\bigcirc	\bigcirc
D	\bigcirc	\bigcirc	\bigcirc	\bigcirc			1	Γ_{OI_I}	5			\bigcirc	\bigcirc	\bigcirc
Е	\bigcirc	\bigcirc	\bigcirc		RFU	(DDF)	Vss	RFU	RFU	RFU		\bigcirc	\bigcirc	\bigcirc
F		\bigcirc	\bigcirc		(VDDF)					RFU		\bigcirc	\bigcirc	\bigcirc
onfident G	\bigcirc	\bigcirc	RFU		Vss					RFU		\bigcirc	\bigcirc	\bigcirc
Н	\bigcirc	\bigcirc	\bigcirc		Data					Vss	gSY	\bigcirc	\bigcirc	\bigcirc
J	\bigcirc	\bigcirc	\bigcirc		Vss)	(DDA	0	\bigcirc	\bigcirc	\bigcirc
K	\bigcirc	\bigcirc	\bigcirc		RSTN	RFU	RFU	Vss	(DDF)	RFU		\bigcirc	\bigcirc	\bigcirc
L	\bigcirc											\bigcirc	\bigcirc	\bigcirc
COM	0		\bigcirc	VDD	CMD	CLK	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc
N	\bigcirc	Vss	\bigcirc	VDD	Vss	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc	\bigcirc
Р	\bigcirc	\bigcirc	VDD	Vss	VDD	Vss	RFU	\bigcirc	\bigcirc	RFU	\bigcirc	\bigcirc	\bigcirc	\bigcirc
			ı	BGA1	53 - E	Ball Ar	ray (I	Ball sid	de dov	wn vie	ew)	L	ng	sys

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6.2 Ball Array view

. 1	Signal	Description
	CLOCK	Each cycle of the clock directs a transfer on the command line and on the data
	(CLK)	lines.
		This signal is a bidirectional command channel used for device initialization and
		command transfer.
	COMMAND	The CMD Signal has 2 operation modes: open drain, for initialization, and push-
	(CMD)	pull, for command transfer.
		Commands are sent from the host to the device, and responses are sent from the
		device to the host.
		These are bidirectional data signal. The DAT signals operate in push-pull mode.
		By default, after power-up or RESET, only DATO is used for data transfer. The
		controller can configure a wider data bus for data transfer wither using DAT
	DATA + 121	[3:0](4bit mode)or DAT[7:0](8bit mode).
	(DATO-DAT7)	Includes internal pull-up resistors for data lines DAT[7:1].Immediately after
7		entering the 4-bit mode, the device disconnects the internal pull-up resistors on
/		the DAT1 and DAT2 lines.(The DAT3 line internal pull-up is left connected.)Upon
		entering the 8bit mode, the device disconnects the internal pull-up on the DAT1,
		DAT2, and DAT[7:4]lines.
	Data Strobe	Newly assigned pin for HS400 mode. Data Strobe is generated from e.MMC to
	(DS)	host.
	(03)	In HS400 mode, read data and CRC response are synchronized with Data Strobe.
	RESET	Hardware Reset Input
	(RSTN)	Fraidware Neset Input
	Vccq	Vccq is the power supply line for host interface, have two power mode: High power
	vecq	mode:2.7V~3.6V; Lower power mode:1.7V~1.95V
	Vcc	Vcc is the power supply line for internal flash memory, its power voltage range
	VCC	is:2.7V~3.6V
	VDDi	VDDi is internal power node, not the power supply. Connect 1uF capacitor VDDi
	VDDi	to ground
	Vss,Vssq	Ground lines.

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Note:

NC: No Connect, shall be connected to ground or left floating.

RFU: Reserved for Future Use, must be left floating for future use.

VSF: Vendor Specific Function, must be left floating.





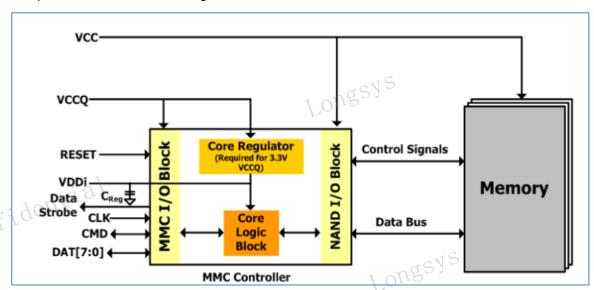


7. Usage Overview

7.1 General description

The eMMC can be operated in 1, 4, or 8-bit mode. NAND flash memory is managed by a controller inside, which manages ECC week leveling and the controller inside, which manages ECC, wear leveling and bad block management. The eMMC provides easy integration with the host process that all flash management hassles are invisible to the host.

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7.2 Partition Management

The embedded device offers also the possibility of configuring by the host additional split local memory partitions with independent addressable space starting from logical address 0x00000000 for different usage models. Default size of each Boot Area Partition is 4096 KB and can be changed by Vendor Command as multiple of 128KB. Boot area partition size is calculated as (128KB * BOOT_SIZE_MULTI) The size of Boot Area Partition 1 and 2 cannot be set independently and is set as same value Boot area partition which is enhanced partition. Therefore memory block area scan is classified as follows:

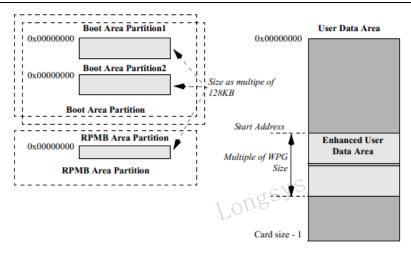
- Factory configuration supplies boot partitions.
- The RPMB partition is 4MB.
- The host is free to configure one segment in the User Data Area to be implemented as enhanced storage media, and to specify its starting location and size in terms of Write Protect Groups. The attributes of this Enhanced User Data Area can be programmed only once during the device lifecycle (one-time programmable).
- Up to four General Purpose Area Partitions can be configured to store user data or sensitive data, or for other host usage models. The size of these partitions is a multiple of the write protect group. Size and attributes can be programmed once in device life-cycle (one-time programmable). Each of the General Purpose Area Partitions can be implemented with enhanced technological features.







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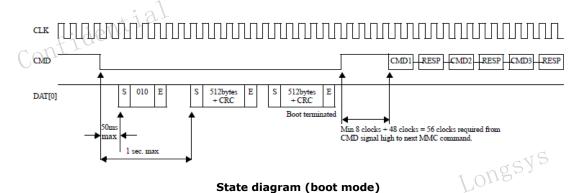
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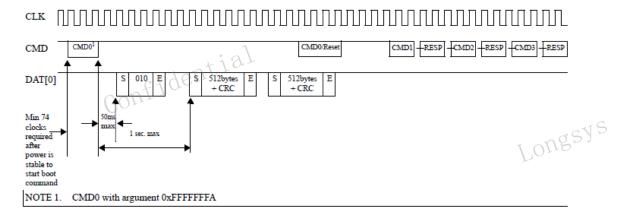
Partitions and user data area configuration

(The size of RPMB area partition is 4MB)

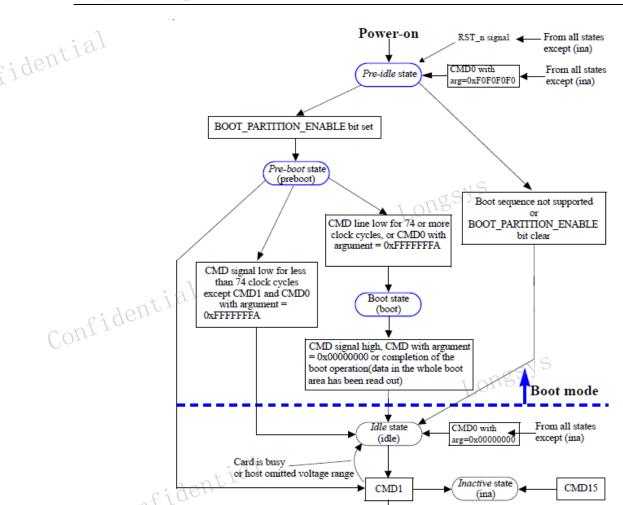
In boot operation mode, the master can read boot data from the slave (device) by keeping CMD line low or sending CMD0 with argument + 0xFFFFFFFA, before issuing CMD1. The data can be read from either boot area or user area depending on register setting.

Timing Factor	Value
Boot ACK Time	< 50 ms
Boot Data Time	< 1 s
Initialization Time	< 1 s





State diagram (alternative boot mode)



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State diagram (boot mode)*

7.3 Automatic Sleep Mode

If host does not issue any command during certain duration (1s), after previously issued command is completed, the device enters "Power Saving mode" to reduce power consumption. At this time, commands arriving at the device while it is in power saving mode will be serviced in normal fashion. The below table explains the condition to enter and exit Auto Power Saving Mode

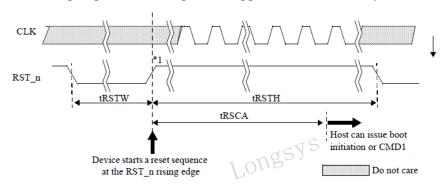
7.4 Sleep (CMD5)

A card may be switched between a Sleep state and a Standby state by SLEEP/AWAKE (CMD5). In the Sleep state the power consumption of the memory device is minimized. In this state the memory device reacts only to the commands RESET (CMD0 with argument of either 0x000000000 or 0xF0F0F0F0 or H/W reset) and SLEEP/AWAKE (CMD5). All the other commands are ignored by the memory device. The timeout for state transitions between Standby state and Sleep state is defined in the EXT_CSD register S_A_timeout. The maximum current consumptions during the Sleep state are defined in the EXT_CSD registers S_A_VCC and S_A_VCCQ. Sleep command: The bit 15 as set to 1 in SLEEP/ AWAKE (CMD5) argument. A wake command: The bit 15 as set to 0 in SLEEP/AWAKE (CMD5) argument.

7.5 H/W Reset operation

Device will detect the rising edge of RST_n signal to trigger internal reset sequence

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H/W reset waveform

7.6 High-speed mode selection

After the host verifies that the card complies with version 4.0, or higher, of this standard, it has to enable the high speed mode timing in the card, before changing the clock frequency to a frequency higher than 20MHz. For the host to change to a higher clock frequency, it has to enable the high speed interface timing. The host uses the SWITCH command to write 0x01 to the HS_TIMING byte, in the Modes segment of the EXT_CSD register.

7.7 Bus width selection

After the host has verified the functional pins on the bus it should change the bus width configuration accordingly, using the SWITCH command. The bus width configuration is changed by writing to the BUS_WIDTH byte in the Modes Segment of the EXT_CSD register (using the SWITCH command to do so). After power-on, or software reset, the contents of the BUS_WIDTH byte is 0x00.

7.8 Partition configuration

Model	Area/Partition	Size	Size	Size	Size	Size (Hex,		
Model	Area/Partition	(GB)	(MB)	(Sector)	(Byte)	∫ ^S Byte)		
FEMKNN004G-58A42	User	3.65GB	3740	7659520	3921674240	E9C00000		
	Boot Partition 1	-	4	8192	4194304	400000		
	Boot Partition 2	-	4	8192	4194304	400000		
	RPMB	√ -	4	8192	4194304	400000		
7.9 CID register fidential								

7.9 CID register

The Card Identification (CID) register is 128 bits wide. It contains the card identification information used during the card identification phase (protocol). Every individual flash or I/O card shall have an unique identification number. Every type of ROM cards (defined by content) shall have a unique identification number. The structure of the CID register is defined in the following sections.

Name	Field	Width	CID-slice	CID Value	Remark
Manufacturer ID	MID	8	[127:120]	D6h	
Reserved	-	6	[119:114]		
Card/BGA	CBX	ci den	[113:112]	01h	BGA





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	Name	Field	Width	CID-slice	CID Value	Remark				
	OEM/Application ID	OID	8	[111:104]	03h					
dent	Product name	PNM	48	[103:56]	0x353841343231	58A421				
Toro	Product revision	PRV	8	[55:48]						
	Product serial number	PSN	32	[47:16]		Not Fixed				
	Manufacturing date	MDT	8	[15:8]		Not Fixed				
	CRC7 checksum	CRC	7	[7:1]		Not Fixed				
	Not used, always '1'	-	1	[0:0]						
	7.10 CSD register									
	7.10 CSD register			1.0112						

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7.10 CSD register

The Card-Specific Data (CSD) register provides information on how to access the card contents. The CSD defines the data format, error correction type, maximum data access time, data transfer speed, whether the DSR register can be used etc. The programmable part of the register (entries marked by W or E, see below) can be changed by CMD27. The type of the CSD Registry entries coded as follows:

Name	Field	Width	Cell Type	CSD-slice
CSD structure	CSD_STRUCTURE	2	R	[127:126]
System specification version	SPEC_VERS	4	rs R	[125:122]
Reserved	-	1295	R	[121:120]
Data read access-time 1	TAAC	8	R	[119:112]
Data read access-time 2 in CLK cycles (NSAC*100)	NSAC	8	R	[111:104]
Max. bus clock frequency	TRAN_SPEED	8	R	[103:96]
Card command classes	CCC	12	R	[95:84]
Max. read data block length	READ_BL_LEN	4	R	[83:80]
Partial blocks for read allowed	READ_BL_PARTIAL	1	R	[79:79]
Write block misalignment	WRITE_BLK_MISALIGN	1	R	[78:78]
Read block misalignment	READ_BLK_MISALIGN	1	R	[77:77]
DSR implemented	DSR_IMP	1	R	[76:76]
Reserved	-	2	R	£75:74]
Device size	C_SIZE	12	1 ROTIS	[73:62]
Max. read current $@_{V_{DD}}$ min	VDD_R_CURR_MIN	3	R	[61:59]
Max. read current $@_{V_{\scriptscriptstyle DD}}$ max	VDD_R_CURR_MAX	3	R	[58:56]
Max. write current $@_{V_{\scriptscriptstyle DD}}$ min	VDD_W_CURR_MIN	3	R	[55:53]
Max. write current $@_{V_{\scriptscriptstyle DD}}$ max	VDD_W_CURR_MAX	3	R	[52:50]
Device size multiplier	C_SIZE_MULT	3	R	[49:47]
Erase group size	ERASE_GRP_SIZE	5	R	[46:42]
Erase group size multiplier	ERASE_GRP_MULT	5	R	[41:37]
Write protect group size	WP_GRP_SIZE	5	R	[36:32]
Write protect group enable	WP_GRP_MULT	1	R	[31:31]
Manufacturer default ECC	DEFAULT_ECC	2	R	[30:29]
Write speed factor	R2W_FACTOR	3	R	[28:26]
Max. write data block length	WRITE_BL_LEN	4	R	[25:22]
Partial blocks for write allowed	WRITE_BL_PARTIAL	1	R	[21:21]





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_					
	Name	Field	Width	Cell Type	CSD-slice
	Reserved	-	4	R	[20:17]
ident!	Content protection application	CONTENT_PROT_APP	1	R	[16:16]
1100	File format group	FILE_FORMAT_GRP	1	R/W	[15:15]
	Copy flag(OTP)	COPY	1	R/W	[14:14]
	Permanent write protection	PERM_WRITE_PROTECT	1	R/W	[13:13]
	Temporary write protection	TMP_WRITE_PROTECT	1	R/W/E	[12:12]
	File format	FILE_FORMAT	2	R/W	[11:10]
	ECC code	ECC	VS 2	R/W/E	[9:8]
	CRC	CRC 10119	7	R/W/E	[7:1]
	Not used, always '1'	-	1	-	[0:0]

7.11 Extended CSD register

The Extended CSD register defines the card properties and selected modes. It is 512 bytes long. The most significant 320 bytes are the Properties segment, which defines the card capabilities and cannot be modified by the host. The lower 192 bytes are the Modes segment, which defines the configuration the card is working in. These modes can be changed by the host by means of the SWITCH command.

Name	Field	Size	Туре	Slice [bytes]	Value	Description
	Reserved			[511:50 6]	-	
Extended security error	EXT_SECURITU_ERR	1	R	[505]	0	
Supported Command Sets	S_CMD_SET	1	R	[504]	1h	
HPI Features	HPI_FEATURES	1	R	[503]	1h	
Background operations support	BKOPS_SUPPORT	1	R	[502]	1h	BKOPS supported
Max packed read command	MAX_PACKED_READS	1	R	[501]	3Fh	
Max packed write command	MAX_PACKED_WRITES	1	R	[500]	3Fh	
Data Tag Support	DATA_TAD_SUPPORT	1	R	[499]	1h	Longsys
Tag Unit Size	TAG_UNIT_SIZE	1	R	[498]	3h	Do
Tag Resource Size	TAG_RES_SIZE	1	R	[497]	0h	



-							
	Name	Field	Size	Туре	Slice [bytes]	Value	Description
	Context management capabilities	CONTEXT_CAPABITILIT IES	1	R	[496]	5h	
	Large Unit size	LARGE_UNIT_SIZE_M1	1	R	[495]	7h	Large Unit size 8MB
	Extended partitions attribute support	EXT_SUPPORT	1	R	g [494]	3h	
	Supported modes	SUPPORTED_MODES	1	R	[493]	3h	
	FFU features	FFU_FEATURES	1	R	[492]	0h	
	Operation codes timeout	OPERATION_CODE_TI MEOUT	1	R	[491]	0h	
	FFU Argument	FFU_ARG	4	R	[490:487]	.0h	
	Barrier support	BARRIER_SUPPORT	1	R	[486]	0h	
	-	Reserved	177	-	[485:309]	-	
	CMDQ support	CMDQ_SUPPORT	1	W/R	[308]	1h	
	CMDQ depth	CMDQ_DEPTH	1	W/R	[307]	1Fh	
	confil	Reserved	1	-	[306]	-	
	Number of received sectors	NUMBER_OF_RECEIVE D_SECTORS	4	R	[305:30 2]	0h	
	Vendor proprietary health report	VENDOR_PROPRIETARY _HEALTH_REPORT	1	R	[301:27 0]	0h	gsys
t t t t t t t t t t t t t t t t t t t	Device life time estimation type B	DEVICE_LIFE_TIME_ES T_TYP_B	1	R	[269]	1h	
	Device life time estimation type A	DEVICE LIFE_TIME_ES T_TYP_A	1	R	[268]	1h	Longsy
	Pre EOL information	PRE_EOL_INFO	1	R	[267]	1h	Pone
	Optimal read size	OPTIMAL_READ_SIZE	1	R	[266]	0h	
	Optimal write size	OPTIMAL_WRITE _SIZE	dent	1 a l	[265]	20h	



Name	Field	Size	Туре	Slice [bytes]	Value	Description
Optimal trim unit size	OPTIMAL_TRIM_UNIT_ SIZE	1	R	[264]	1h	
Device version	DEVICE_VERSION	2	R	[263:262]	0h	
Firmware version	FIRMWARE_VERSION	8	R	[261:254]	-	
Power class for200MHz, DDR at VCC=3.6V	PWR_CL_DDR_200_36 0	1	R	g [253]	0h	
Cache size	CACHE_SIZE	4	R	[252:24 9]	10000h	
Generic CMD6 timeout	GENERIC_CMD6_TIME	1	R	[248]	Ah	
Power-off notification(lo ng) timeout	POWER_OFF_LONG_TI ME	1	R	[247]	3Ch	
Background operations status	BKOPS_STATUS	1	R	[246]	0h	No operations required
Number of correctly programmed sectors	CORRECTLY_PRG_SECT ORS_NUM	4	R	[245:242]	0h	
First Initialization time after partitioning	INI_TIMEOUT_AP	1	R	[241]	1Eh	. T. G
Cache Flushing Policy	CACHE_FLUSH_POLIC Y	1	R	[240]	ohlon	gSy
Power class for 52Mhz,DDR at 3.6V	PWR_CL_DDR_52_360	a.1	R	[239]	0h	
Power class for 52Mhz,DDR at 1.95V	PWR_CL_DDR_52_195	1	R	[238]	0h	Longsys
Power class for 200Mhz at	PWR_CL_200_195	1	R	[237]	0h	



Name	Field	Size	Туре	Slice [bytes]	Value	Description
Power class for 200Mhz at VCCQ=1.3V, VCC=3.6V	PWR_CL_200_360	1	R	[236]	0h	
Minimum write performance for 8bit at 52MHz in DDF	MIN_PERF_DDR_W_8 _52	1	R	_O [235]	0h	
Minimum read performance for 8bit at 52MHz in DDF mode	MIN_PERF_DDR_R_8_	1	R	[234]	0h	
	Reserved	1	-	[233]	15 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
TRIM Multiplier	TRIM_MULT	1	R	[232]	5h	
Secure feature support	SEC_FEATURE_SUPPORT Confidenti	1	R	[231]	55h	3. Secure purge operations are supported. 4. Support the sanitize operation
Secure Erase Multiplier	SEC_ERASE_MULT	1	R	[230]	1Bh	Longsys
Secure TRIM Multiplier	SEC_TRIM_MULT	1	R	[229]	11h	





Name	Field	Size	Туре	Slice [bytes]	Value	Descriptio
Boot Information	BOOT_INFO	1	R	[228]	7h	1. Support speed till boot. 2. Support data ratill during b 3. Support alternatill boot me
F	Reserved	1	-	[227]	-	
Boot partition size	BOOT_SIZE_MULTI	1	R	[226]	20h	boot partition 4096KB
Access size	ACC_SIZE	1	R	[225]	6h	super page 16KB
High-capacity Erase unit size	HC_ERASE_GROUP_SI ZE	1	R	[224]	ISY Sh	hc erase gro size 512KB
High-capacity Erase time out	ERASE_TIMEOU_MULT	1	R	[223]	5h	
Reliable write sector count	REL_WR_SEC_C	1	R	[222]	1h	1 sector
High-capacity write protect group size	HC_WP_GRP_SIZE	1	R	[221]	8h	hc wp grou size 4096KI
Sleep current(VCC)	S_C_VCC	1	R	[220]	7h	
Sleep current[VCCQ]	s_c_vccq	1	R	[219]	7h	gsys
Production state awareness timeout	PRODUCTION_STATE_ AWARENESS_TIMEOU T	1	R	[218]	0h	Not defined
Sleep/Awake time out	s_a_timeoutlent1	1	R	[217]	16h	
Sleep Notification Time out	SLEEP_NOTIFICATION _TIME	1	R	[216]	10h	Long
Sector count	SEC_COUNT	4	R	[215:212]	74E000h	
Secure Write Protection Mode	SECURE_WP_INFO	dent	ial	[211]	1h	



Minimum Write Performance for 8bit @52MHz Minimum Read Performance for 8bit MIN_PERF_R_8_52 1 Minimum Write Reformance for 4bit MIN_PERF_W_8_26_4 1 Performance for 4bit MIN_PERF_R_8_26_4 1 R @52MHz or 8bit @26MHz MIN_PERF_R_8_26_4 1 R [208] Minimum Read Performance for 4bit 52 1 R [207] Minimum Write N Performance for 4bit N P <td< th=""><th></th><th>Name</th><th>Field</th><th>Size</th><th>Туре</th><th>Slice [bytes]</th><th>Value</th><th>Description</th></td<>		Name	Field	Size	Туре	Slice [bytes]	Value	Description
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Performance for 8bit @52MHz MIN_PERF_W_8_52 1 R [210] [209] R [209] [208] [2								
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Minimum Read Performance for 8bit @52MHz Minimum Write Performance for 4bit @52MHz or 8bit @26MHz Minimum Write Performance for 4bit @52MHz or 8bit @26MHz Minimum Write Performance for 4bit @652MHz or 8bit @26MHz Minimum Write Performance for 4bit @26MHz Minimum Read Performance for 4bit @26MHz Minimum Read Performance for 4bit @36MHz PERF_W_4_26 1 R [206] Reserved 1 - [204] Power Class for 26MHz @3.6V Power Class for 52MHz @3.6V Power Class for 26MHz PWR_CL_52_360 1 R [202] [202]								
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for 4bit	M	linimum Write						
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@1.95V			PWR_CL_26_195	1	R	[201]	0h	
antider	(⊉1.95V		1 ont	jal			
			anfi	gen,				
www.longsvs.com Page 16 Lo	_		Coll					Electronics



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Name	Field	Size	Туре	Slice [bytes]	Value	Description		
Power Class for 52MHz @1.95V	PWR_CL_52_195	1	R	[200]	0h			
Partition switching timing	PARTITION_SWITCH_T IME	1	R	[199]	Ah			
Out-of- interrupt busy timing	OUT_OF_INTERRUPT_T IME	1	Ron	S[198]	5h			
I/O Driver Strength	DRIVER_STRENGTH	1	R	[197]	1Fh			
Card Type	CARD_TYPE	1	R	[196]	57h	HS400 DDR eMMC@200Mhz -1.8V I/O		
	Reserved	1	-	[195]	- 15 S			
CSD Structure Version	CSD_STRUCTURE	1	R	[194]	2h			
	Reserved	1	-	[193]	-			
Extended CSE Revision	EXT_CSD_REV	1	R	[192]	8h			
Command Se	CMD_SET	1	R/W/E _P	[191]	0h			
0,-,	Reserved	1	-	[190]	-			
Command set revision	: CMD_SET_REV	1	R	[189]	0h			
	Reserved	1	-	[188]	-			
Power class	POWER_CLASS	1	R/W/E _P	[187]	Oh ON	gSYS		
	Reserved	1	-	[186]	-			
High Speed Interface Timing	HS_TIMING	1 a.l	R/W/E _P	[185]	0h			
Strobe Support	STROBE_SUPPORT	1	R	[184]	1h			
Bus Width Mode	BUS_WIDTH	1	W/E_P	[183]	0h	Longsys		
	Reserved	1	-	[182]	-	Do		
Erased memory range	ERASE_MEM_CONT	1	R	[181]	0h			
<u> </u>	Reserved	1 ont	197	[180]	-			



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_							
• 1	Name	Field	Size	Туре	Slice [bytes]	Value	Description
, 1	Partition Configuration	PARTITION_CONFIG	1	R/W/E R/W/E _P	[179]	0h	
_	Boot config protection	BOOT_CONFIG_PROT	1	R/W R/W/C _P	[178]	0h	
	Boot bus width1	BOOT_BUS_WIDTH	1	R/W/E	g [177]	0h	
		Reserved	1	-	[176]	-	
	High-density erase group definition	ERASE_GROUP_DEF	1	R/W/E _P	[175]	0h	
JC.	Boot write protection status registers	BOOT_WP_STATUS	1	R	[174]	Oh gSYS	
	Boot area write protect register	BOOT_WP	1	R/W R/W/C _P	[173]	0h	
		Reserved 1	1	-	[172]	-	
	User area write protect register	USER_WP	1	R/W R/W/C _P R/W/E _P	[171]	0h	
Ī		Reserved	1	-	[170]	-	
	FW Configuration	FW_CONFIG	1	R/W	[169]	0h	gSYS
	RPMB Size	RPMB_SIZE_MULT	1	R	[168]	20h	RPMB size is 4MB
	Write reliability setting register	WR_REL_SET confidenti	al ₁	R/W	[167]	1Fh	
	Write reliability parameter register	WR_REL_PARAM	1	R	[166]	15h	Support the enhanced definition of reliable write
	Start Sanitize operation	SANITIZE_START	1	W/E_P	[165]	0h	

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_							
• 1	Name	Field	Size	Туре	Slice [bytes]	Value	Description
4	Manually start background operations	BKOPS_START	1	W/E_P	[164]	0h	
	Enable background operations handshake	BKOPS_EN	1	R/W	[163]	0h	
	H/W reset function	RST_n_FUNCTION	1	R/W	[162]	0h	
	HPI management	HPI_MGMT	1	R/W/E _P	[161]	0h	
,01	Partitioning support	PARTITIONING_SUPP ORT	1	R	[160]	SSYS 7h	1. Enhanced technological features in partitions and user data area. 2. Device supports partitioning features 3. Device can have extended partition attribute
	Max Enhanced Area Size	MAX_ENH_SIZE_MULT	3	R	[159:15 7]	-	TBD
	Partitions attribute	PARTITIONS_ATTRIBU TE	1	R/W	[156]	0h	gsy ^s
	Partitions setting	PARTITIONS_SETTING _COMPLETED	1	R/W	[155]	0h	
	General Purpose Partition Size	GP_SIZE_MULT	12	R/W	[154:14 3]	0h	
	Enhanced User Data Area Size	ENH_SIZE_MULT	3	R/W	[142:14 0]	0h	- 2575
	Enhanced User Data Start Address	ENH_START_ADDR	4	R/W	[139:13 6]	0h	Polis.
	Start Address						

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	Name	Field	Size	Туре	Slice [bytes]	Value	Description	
	Secure Bad Block Management Mode	SEC_BAD_BLK_MGMN T	1	R/W	[134]	0h		
	Production state awareness	PRODUCTION_STATE_ AWARENESS	1	R/W/E	[133]	0h		
	Package Case Temperature is controlled	TCASE_SUPPORT	1	W/E_P	[132]	0h		
	Periodic Wake-up	PERIODIC_WAKEUP	1	R/W/E	[131]	0h		
01	Program CID/CSD in DDR mode support	PROGRAM_CID_CSD_ DDR_SUPPORT	1	R	[130]	1h		
	I	Reserved	2	-	[129:12 8]	-		
	Vendor specific field	VENDOR_SPECIFIC_FI	64	<pre><vend or="" specfic=""></vend></pre>	[127:64]	0h		
	Native sector size	NATIVE_SECTOR_SIZ E	1	R	[63]	0h		
	Sector size emulation	USE_NATIVE_SECTOR	1	R/W	[62]	0h		
	Sector size	DATA_SECTOR_SIZE	1	R	[61]	0h	-7 C	
	1st initialization after disabling sector size emulation	INI_TIMEOUT_EMU	1	R	[60]	Oh Oh	gSY -	
_	Class 6 commands control	CLASS 6 CTRL	1	R/W/E _P	[59]	0h		
	Number of addressed group to be Released	DYNCAP_NEEDED	1	R	[58]	0h	Longsy	
	Exception events control	EXCEPTION_EVENTS_ CTRL	2	R/W/E	[57:56]	0h		
		confi confi	gen,					
_	www.lona			age 20		Longsvs	Electronics	



				Slice			
Na	ame	Field	Size	Туре	[bytes]	Value	Description
Except events	ion status	EXCEPTION_EVENTS_ STATUS	2	R	[55:54]	0h	
Extend Partition Attribu	ons	EXT_PARTITIONS_ATT RIBUTE	2	R/W	[53:52]	0h	
Contex	kt uration	CONTEXT_CONF	15	R/W/E _P	[51:37]	0h	
Packed commo		PACKED_COMMAND_S TATUS	1	Lon	[36]	0h	
Packed common failure	and	PACKED_FAILURE_IN	1	R	[35]	0h	
Power Notific		POWER_OFF_NOTIFIC ATION	1	R/W/E _P	[34]	0h	
Contro turn th Cache		ON/OFF CACHE_CTRL	1	R/W/E _P	[33]	0h	
Flushir the ca	_	FLUSH_CACHE	1	W/E_P	[32]	0h	
Contro turn th Barrier ON/OF	enfi	ON/OFF BARRIER_CTRL	1	R/W	[31]	0h	
Mode o	config	MODE_CONFIG	1	R/W/E _P	[30]	0h	
Mode operat codes	ion	MODE_OPERATION_C ODES	1	W/E_P	[29]	Oh On	gsys
	ı	Reserved	2	-	[28:27]	-	
FFU st	atus	FFU_STATUS	1	R	[26]	0h	
Pre loa	_	PRE_LOADING_DATA_ SIZE	a]4	R/W/E _P	[25:22]	0h	
Max prolong loading size		MAX_PRE_LOADING_ DATA_SIZE	4	R	[21:18]	-	Longsys
Produc awarei enable		PRODUCT_STATE_AW ARENESS_ENABLEME NT	1	R/W/E &R	[17]	0h	Pone
Secure	e val Type	SECURE_REMOVAL_TY PE	1	R/W&	[16]	9h	





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Name	Field	Size	Туре	Slice [bytes]	Value	Description
Command Queue Mode Enable	CMDQ_MODE_EN	1	R/W/E _P	[15]	0h	
	15	-	[14:0]	-		

Notes:

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.. R= Read-only

R/W=One-Time Programmable and readable

R/W/E=Multiple writable with value kept after a power cycle, assertion of the RST_n signal, and any

CMD0 reset, and readable

TBD=To Be Defined.

2. Reserved bits should be read as 0.

7.12 OCR Register

The 32-bit operation conditions register stores the VCCQ voltage profile of the eMMC. In addition, this register includes a status information bit. This status bit is set if the eMMC power up procedure has been finished. The OCR register shall be implemented by eMMC.

OCR bit	VCCQ voltage window	eMMC
[6:0]	Reserved	000 0000Ь
[7]	1.7-1.95	1b
[14:8]	2.0-2.6	000 0000Ь
[23:15]	2.7-3.6	1 1111 1111b
[28:24]	Reserved	000 0000Ь
[30:29]	Access Mode	00b (byte mode)/10b (sector
0012		mode)
[31]	power up stat	us bit (busy)*

Note*: This bit is set to LOW if the eMMC has not finished the power up routine. The supported voltage range is coded as shown in table.

7.13 Field firmware update(FFU)

To download a new firmware, the controller requires instruction sequence following JEDEC standard. Longsys eMMC only supports Manual mode (MODE_OPERATION_CODES is not supported). For more details, refer to the App note.

Longsys eMMC (NCEMAD9D-xxG) Field F/W update flow - CMD sequence

Operation	CMD	Remark
Set block length 512B	CMD16, arg:	
	0x00000200	
Enter FFU mode	CMD6, arg: 0x031E0100	angsyp
Send FW to	CMD25, arg:	Sending CMD25 is followed by sending FW
device(Download)	0x00000000	data ,The whole data should be sent by one
		CMD25
CMD12 : Stop	CMD12, arg:	1
	0x00000000 + 1	, 1
CMD6 : Exit FFU mode	CMD6, arg: 0x031E0000	



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HW Reset/	Power cycle		CMD0 Reset is not support
Re-Init to	trans state	CMD0, CMD1	
100			Check EXT_CSD[26]: FFU_SUCCESS
Check	if FFU is	CMD8, arg: 0x00000000	If FFU_SUCCESS is 0, FFU is succeeded,
succe	eeded		otherwise FFU is failed.
			Do not verify data with CMD17/CMD18 while FFU
			mode.

Longsys

SUPPORTED_MODE[493] (Read Only)

BIT[0]: '0' FFU is not supported by the device.

'1' FFU is supported by the device.

BIT[1]: '0' Vendor specific mode (VSM) is not supported by the device.

'1' Vendor specific mode is supported by the device.

	Bit	Field	Supportability
	Bit[7:2]	Reserved	•
cont	Bit[1]	VSM	Not support
	Bit[0]	FFU	Support
FFU	_FEATURE[492] (Read Only)	Long'	5)

FFU_FEATURE[492] (Read Only)

BIT[0]: '0' Device does not support MODE_OPERATION_CODES field (Manual mode)

'1' Device supports MODE_OPERATION_CODES field (Auto mode)

Bit	Field	Supportability
Bit[7:1] 11	Reserved	-
Bit[0]	SUPPORTED_MODE_OPERATION_CODES	Not support
Cor		

FFU_ARG[490-487] (Read Only)

Using this field the device reports to the host which value the host should set as an argument for read and write commands in FFU mode.

FW_CONFIG[169] (R/W)

BIT[0]: Update disable

0x0 : FW updates enabled.

0x1: FW update disabled permanently

Bit	1 Field	Supportability
Bit[7:1]	Reserved	-
Bit[0]	Update disable	FW updates enabled (0x0)

Longsys

FFU_STATUS[26] (R/W/E_P)

Using this field the device reports to the host the state of FFU process

Value	Description
0x13 ~ 0xFF	Reserved
0x12 1 0 0 1 1	Error in downloading



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		Firmware
121	0x11	Firmware install error
	0x10	General error
	0x01 ~ 0x0F	Reserved
	0x00	Success

OPERATION_CODES_TIMEOUT[491](Read Only)

Maximum timeout for the SWITCH command when setting a value to the MODE_OPERATION_CODES field. The register is set to '0', because the controller doesn't support MODE_OPERATION_CODES.

Value	Description	Timeout value
0x01 ~ 0x17	MODE_OPERATION_CODES_TIMEOUT = 100us x	(Not defined)
	2OPERATION_CODES_TIMEOUT	
0x18 ~ 0xFF	Reserved	-

MODE_OPERATION_CODES[29] (W/E_P)

The host sets the operation to be performed at the selected mode, in case MODE_CONFIGS is set to FFU_MODE,MODE_OPERATION_CODES could have the following values:

Value	Description
0x01	FFU_INSTALL
0x02	FFU_ABORT
0x00, others	Reserved

7.14 S.M.A.R.T. Health Report

S.M.A.R.T. is a monitoring system that detects and reports on various indicators of eMMC reliability(Including original bad blocks, increased bad blocks, power-up number, power-loss counts and etc), with the intent of enabling the anticipation of hardware failures. We may be able to use recorded S.M.A.R.T. data to discover where the faults lie, ensure how to solve the problems and prevent them from recurring in future eMMC designs (For details, please refer to app note).







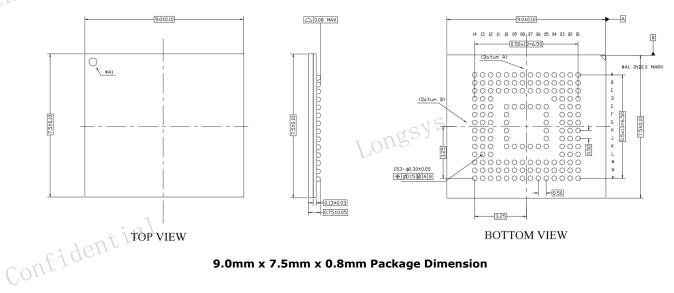




8. Package Dimension

UNIT:mm

Eident



Longsys

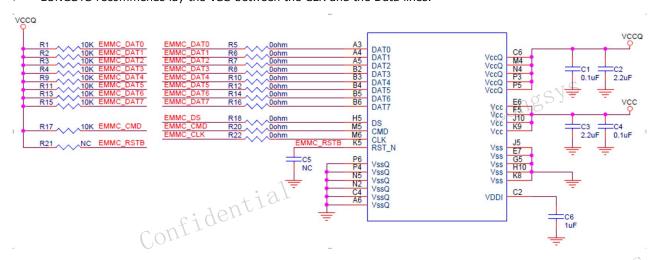
9.0mm x 7.5mm x 0.8mm Package Dimension

Longsys

9 Connection Guide

9.1 Schematic Diagram

- Coupling capacitor should be connected with VCC/VCCQ and VSS as closely as possible.
- The resistance on the CLK line is highly recommended (0 Ω by default). $0\Omega \sim 100\Omega$ is also available.
- LONGSYS recommends to separate VCC and VCCQ power. ▶
- VDDi Capacitor is min 0.1uF.
- ➤ LONGSYS recommends lay the VSS between the CLK and the Data lines.



The resistance on the CLK line is highly recommended (0Ω by default)



10. Processing Guide

It is recommended to follow the instructions of Moisture Sensitivity Level 3.

In the case of Pre-program before SMT, It is highly recommended to limit the size of data pre-programmed to the eMMC, please contact your agency for more information.

The amount of data pre-programmed (data written before SMT) is limited, it should be managed properly.



Maximum size for the data-written to IDA.

idential

Part Number	Size limited for Pre-programmed Data
FEMKNN004G-58A42	1.9GB

Longsys

 Co_{D}

Longsys

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